International

AUTOMOTIVE GRADE

AUIRLL024N

HEXFET[®] Power MOSFET

Features

- Advanced Planar Technology
- Low On-Resistance
- Dynamic dV/dT Rating
- 150°C Operating Temperature
- Fast Switching
- Fully Avalanche Rated
- Repetitive Avalanche Allowed up to Tjmax
- Lead-Free, RoHS Compliant
- Automotive Qualified *

Description

Specifically designed for Automotive applications, this Cellular design of HEXFET® Power MOSFETs utilizes the latest processing techniques to achieve low onresistance per silicon area. This benefit combined with the fast switching speed and ruggedized device design that HEXFET power MOSFETs are well known for, provides the designer with an extremely efficient and reliable device for use in Automotive and a wide variety of other applications.



G	D	S	
Gate	Drain	Source	

Absolute Maximum Ratings

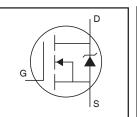
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only; and functional operation of the device at these or any other condition beyond those indicated in the specifications is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability. The thermal resistance and power dissipation ratings are measured under board mounted and still air conditions. Ambient temperature (T_A) is 25°C, unless otherwise specified.

	Parameter	Max.	Units	
I _D @ T _A = 25°C	Continuous Drain Current, V _{GS} @ 10V [®]	4.4		
I _D @ T _A = 25°C	Continuous Drain Current, V _{GS} @ 10V [®]	3.1	•	
I _D @ T _A = 70°C	Continuous Drain Current, V _{GS} @ 10V ^⑤	2.5	A	
I _{DM}	Pulsed Drain Current ①	12		
P _D @T _A = 25°C	Power Dissipation (PCB Mount)®	2.1	W	
P _D @T _A = 25°C	Power Dissipation (PCB Mount)	1.0	W	
	Linear Derating Factor (PCB Mount) ^⑤	8.3	W/°C	
V _{GS}	Gate-to-Source Voltage	± 16	V	
AS Single Pulse Avalanche Energy [®]		120	mJ	
I _{AR}	Avalanche Current ①	3.1	A	
E _{AR}	Repetitive Avalanche Energy 05	0.1	mJ	
dv/dt	Peak Diode Recovery dv/dt 3	5.0	V/ns	
TJ	Operating Junction and	-55 to + 150	°C	
T _{STG}	Storage Temperature Range			

Thermal Resistance

	Parameter	Тур.	Max.	Units
R _{0JA}	Junction-to-Ambient (PCB mount, steady state)	90	120	°C/W
R _{0JA}	Junction-to-Ambient (PCB mount, steady state)®	50	60	0/11

 ${\sf HEXFET}^{\textcircled{B}}$ is a registered trademark of International Rectifier. *Qualification standards can be found at http://www.irf.com/



V _{(BR)DSS}	55V
R _{DS(on)} max.	0.065 Ω
I _D	3.1A

Parameter Min. Тур. Max. Units Conditions Drain-to-Source Breakdown Voltage 55 $V_{GS} = 0V, I_D = 250\mu A$ V_{(BR)DSS} ٧ Reference to 25°C, I_D = 1mA V/°C $\Delta V_{(BR)DSS} / \Delta T_J$ Breakdown Voltage Temp. Coefficient 0.048 ____ V_{GS} = 10V, I_D = 3.1A ④ 0.065 0.080 Ω V_{GS} = 5.0V, I_D = 2.5A ④ R_{DS(on)} Static Drain-to-Source On-Resistance 0.100 V_{GS} = 4.0V, I_D = 1.6A ④ V_{GS(th)} $V_{DS} = V_{GS}, I_D = 250 \mu A$ Gate Threshold Voltage 1.0 2.0 V $V_{DS} = 25V, I_D = 1.9A$ Forward Transconductance 3.3 S gfs _____ Drain-to-Source Leakage Current $V_{\text{DS}} = 55 \text{V}, \, V_{\text{GS}} = 0 \text{V}$ 25 DSS μΑ 250 $V_{DS} = 44V, V_{GS} = 0V, T_{J} = 125^{\circ}C$ Gate-to-Source Forward Leakage 100 $V_{GS} = 16V$ I_{GSS} nA $V_{GS} = -16V$ Gate-to-Source Reverse Leakage -100

Static Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

Dynamic Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

Q _g	Total Gate Charge	 10.4	15.6		I _D = 1.9A
Q _{gs}	Gate-to-Source Charge	 1.5	2.3	nC	$V_{DS} = 44V$
Q _{gd}	Gate-to-Drain ("Miller") Charge	 5.5	8.3		V_{GS} = 5.0V, See Fig 6 and 13 \circledast
t _{d(on)}	Turn-On Delay Time	 7.4			$V_{DD} = 28V$
t _r	Rise Time	 21			I _D = 1.9A
t _{d(off)}	Turn-Off Delay Time	 18		ns	$R_{G} = 24 \Omega$
t _f	Fall Time	 25			$R_D = 15 \Omega$, See Fig. 10 ④
C _{iss}	Input Capacitance	 510			$V_{GS} = 0V$
C _{oss}	Output Capacitance	 140		pF	$V_{DS} = 25V$
C _{rss}	Reverse Transfer Capacitance	 58			f = 1.0MHz,see Fig.5

Diode Characteristics

	Parameter	Min.	Тур.	Max.	Units	Conditions
I _S	Continuous Source Current			3.1		MOSFET symbol
	(Body Diode)			5.1	А	showing the
I _{SM}	Pulsed Source Current			12		integral reverse _G Ų 🏹
	(Body Diode) ①			12		p-n junction diode.
V _{SD}	Diode Forward Voltage			1.0	V	$T_J = 25^{\circ}C, I_S = 1.9A, V_{GS} = 0V$ (4)
t _{rr}	Reverse Recovery Time		39	58	ns	T _J = 25°C, I _F = 1.9A
Q _{rr}	Reverse Recovery Charge		63	94	nC	di/dt = 100A/µs ④
t _{on}	Forward Turn-On Time	Intrinsic	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD)			

Notes:

- ${\rm \textcircled{O}}$ Repetitive rating; pulse width limited by max. junction temperature. (See fig. 11)
- @ Starting T_J = 25°C, L = 25 mH, R_G = 25 $\Omega,$ I_{AS} = 3.1A. (See Figure 12)
- 3 I_{SD} \leq 1.9A, di/dt \leq 270A/µs, V_{DD} \leq V_{(BR)DSS}, T_J \leq 150°C
- ④ Pulse width \leq 300µs; duty cycle \leq 2%.
- ⑤ When mounted on FR-4 board using minimum recommended footprint..
- $\ensuremath{\textcircled{}^{\circ}}$ When mounted on 1 inch square copper board, for comparison with other SMD devices.

Qualification Information[†]

		Automotive (per AEC-Q101) ^{††}				
Qualification	Level	Comments: This part number(s) passed Automoti qualification. IR's Industrial and Consumer qualificati level is granted by extension of the higher Automotive leve				
Moisture Ser	nsitivity Level	SOT-223 MSL1				
Machine Model		Class M2(+/- 150V) ^{†††} (per AEC-Q101-002)				
ESD	Human Body Model	Class H1A(+/- 500V) ^{†††} (per AEC-Q101-001)				
	Charged Device Model	Class C5(+/- 2000V) ^{†††} (per AEC-Q101-005)				
RoHS Compl	liant	Yes				

† Qualification standards can be found at International Rectifier's web site: http://www.irf.com/

tt Exceptions (if any) to AEC-Q101 requirements are noted in the qualification report.

ttt Highest passing voltage

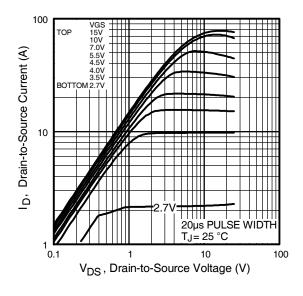


Fig 1. Typical Output Characteristics

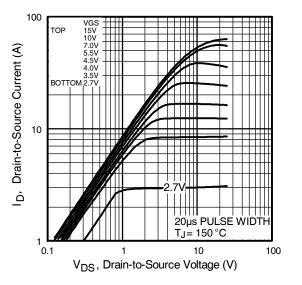


Fig 2. Typical Output Characteristics

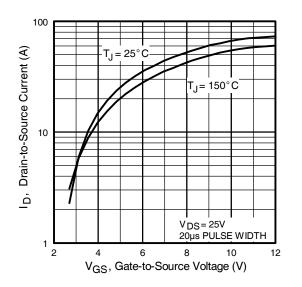


Fig 3. Typical Transfer Characteristics

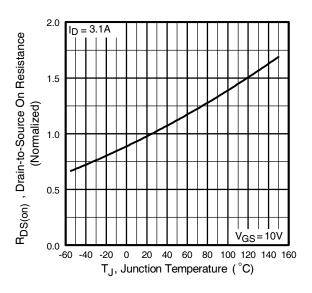


Fig 4. Normalized On-Resistance Vs. Temperature

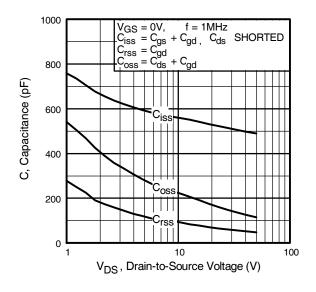


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

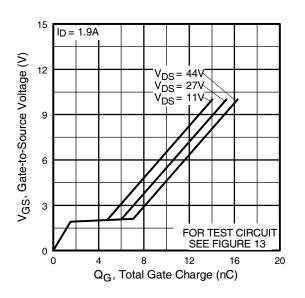
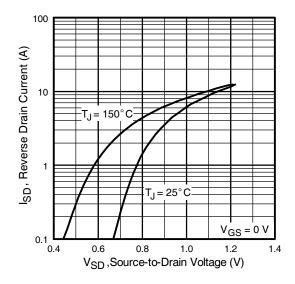


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage





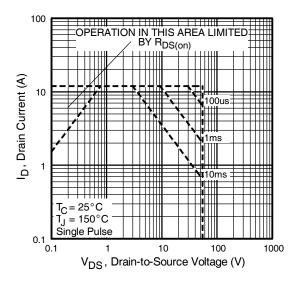
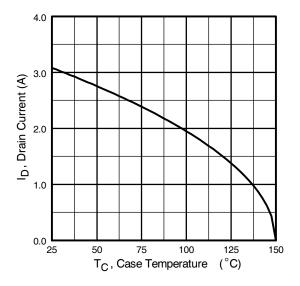
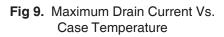
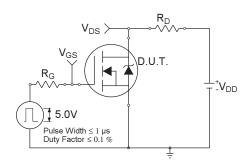


Fig 8. Maximum Safe Operating Area

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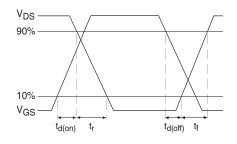


Fig 10b. Switching Time Waveforms

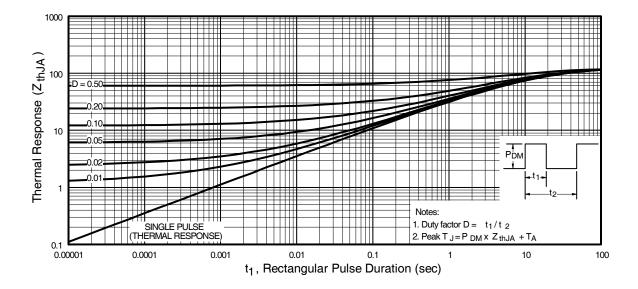


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Ambient

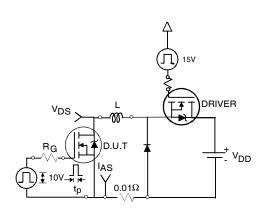


Fig 12a. Unclamped Inductive Test Circuit

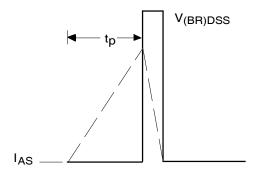


Fig 12b. Unclamped Inductive Waveforms

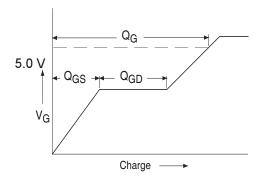
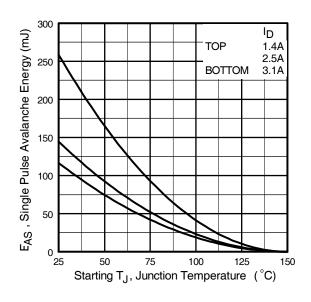
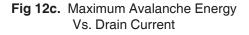


Fig 13a. Basic Gate Charge Waveform





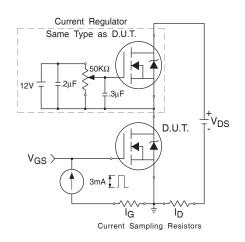
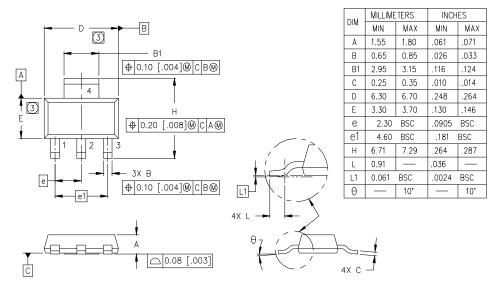


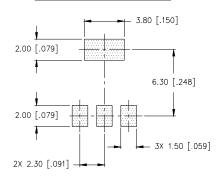
Fig 13b. Gate Charge Test Circuit

SOT-223 (TO-261AA) Package Outline

Dimensions are shown in milimeters (inches)



MINIMUM RECOMMENDED FOOTPRINT



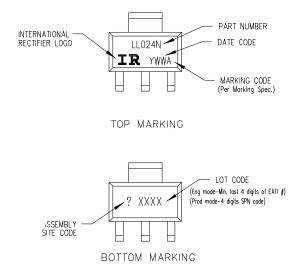
 $\frac{\text{LEAD ASSIGNMENTS}}{1 = \text{GATE}}$

- 1 = GATE 2 = DRAIN
- 3 = SOURCE
- 4 = DRAIN

NOTES:

- 1. DIMENSIONING & TOLERANCING PER ASME Y14.5M-1994.
- 2. CONTROLLING DIMENSION: INCH.
- DIMENSIONS DO NOT INCLUDE MOLD FLASH.
 4. OUTLINE CONFORMS TO JEDEC OUTLINE TO-261AA.
- OUTLINE CONFORMS TO JEDEC OUTLINE TO-261AA.
 DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].

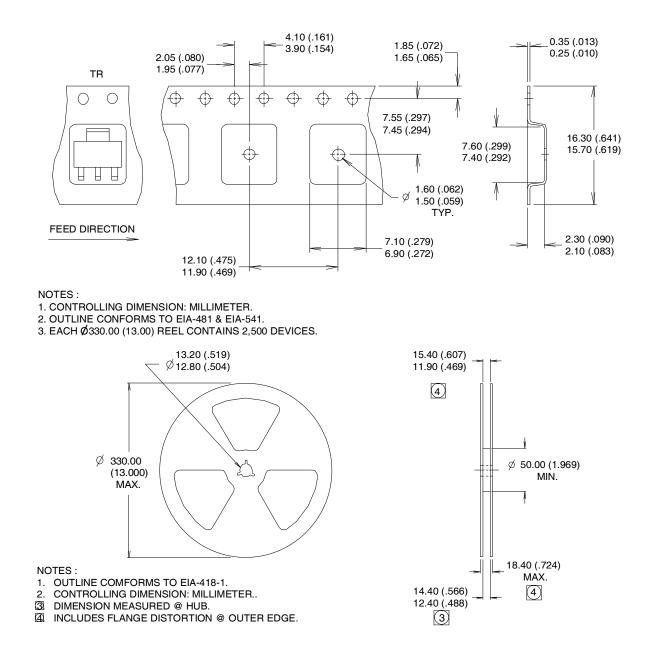
SOT-223 (TO-261AA) Part Marking Information



Note: For the most current drawing please refer to IR website at http://www.irf.com/package/

SOT-223 (TO-261AA) Tape & Reel Information

Dimensions are shown in milimeters (inches)



www.irf.com



Ordering Information

Base part	Package Type	Standard Pack		Complete Part Number
		Form	Quantity	
AUIRLL024N	SOT-223	Tube	95	AUIRLL024N
		Tape and Reel	2500	AUIRLL024NTR

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